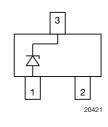


Vishay Semiconductors

## **Single-Line ESD-Protection in SOT-23**





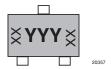
#### **FEATURES**

- Single-line ESD-protection device
- ESD-protection acc. IEC 61000-4-2
  - ± 30 kV contact discharge
  - ± 30 kV air discharge
- Space saving SOT-23 package
- AEC-Q101 qualified
- e3 Sn





#### **MARKING** (example only)



YYY = type code (see table below)

XX = date code

ORDERING INFO	RMATION				
DEVICE NAME	ENVIRONMENTAL STATUS	ORDERING CODE	TAPED UNITS PER REEL (8 mm TAPE ON 7" REEL)	MINIMUM ORDER QUANTITY	
GSOT03	Standard	GSOT03-GS08	3000	15 000	
G30103	Green	GSOT03-G-08	3000	15 000	
GSOT04	Standard	GSOT04-GS08	3000	15.000	
GSU104	Green	GSOT04-G-08	3000	15 000	
GSOT05	Standard	GSOT05-GS08	3000	15 000	
GSO105	Green	GSOT05-G-08	3000	15 000	
GSOT08	Standard	GSOT08-GS08	3000	15 000	
G30100	Green	GSOT08-G-08	3000	13 000	
GSOT12	Standard	GSOT12-GS08	3000	15.000	
G50112	Green	GSOT12-G-08	3000	15 000	
GSOT15	Standard	GSOT15-GS08	3000	15 000	
G30113	Green	GSOT15-G-08	3000	15 000	
CCCT04	Standard	GSOT24-GS08	3000	15.000	
GSOT24	Green	GSOT24-G-08	3000	15 000	
CCCT26	Standard	GSOT36-GS08	3000	15.000	
GSOT36	Green	GSOT36-G-08	3000	15 000	

<sup>\*\*</sup> Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

### **GSOT03 to GSOT36**

## Vishay Semiconductors

# Single-Line ESD-Protection in SOT-23



PACKA	GE DATA						
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
000700		03	Standard	8.8 mg		MSL level 1	222.2011
GSOT03	SOT-23	03G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
000704	007.00	04	Standard	8.8 mg		MSL level 1	200 00 /10
GSOT04	SOT-23	04G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
		05	Standard	8.8 mg		MSL level 1	
GSOT05	SOT-23	05G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
000700		08	Standard	8.8 mg		MSL level 1	222.2011
GSOT08	SOT-23	08G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
000710		12	Standard	8.8 mg		MSL level 1	
GSOT12	SOT-23	12G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
		15	Standard	8.8 mg		MSL level 1	
GSOT15	SOT-23	15G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
000704		24	Standard	8.8 mg		MSL level 1	
GSOT24	SOT-23	24G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
000700	227.22	36	Standard	8.8 mg		MSL level 1	
GSOT36	SOT-23	36G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals

ABSOLUTE MAXIMUM RATINGS GSOT03				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	I <sub>PPM</sub>	30	Α
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	P <sub>PP</sub>	369	W
CCD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	± 30	kV
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C

ABSOLUTE MAXIMUM RATINGS GSOT04				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	I <sub>PPM</sub>	30	Α
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	P <sub>PP</sub>	429	W
ECD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	± 30	kV
Operating temperature	Junction temperature	T <sub>J</sub>	- 40 to + 125	°C
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C





# Single-Line ESD-Protection in SOT-23

## Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS GSOT05				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	I <sub>PPM</sub>	30	А
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	P <sub>PP</sub>	480	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV
L3D illillidility	Air discharge acc. IEC 61000-4-2; 10 pulses	- V <sub>ESD</sub>	± 30	kV
Operating temperature	Junction temperature	T <sub>J</sub>	- 40 to + 125	°C
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C

ABSOLUTE MAXIMUM RATINGS GSOT08					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	I <sub>PPM</sub>	18	А	
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	P <sub>PP</sub>	345	W	
ECD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	± 30	kV	
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	± 30	kV	
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C	
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT12					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	I <sub>PPM</sub>	12	Α	
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	P <sub>PP</sub>	312	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	± 30	kV	
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C	
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT15					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	I <sub>PPM</sub>	8	Α	
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	P <sub>PP</sub>	230	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV	
E3D Illillidility	acc. IEC 61000-4-5, $t_p$ = 8/20 $\mu$ s; single shot  Contact discharge acc. IEC 61000-4-2; 10 pulses  Air discharge acc. IEC 61000-4-2; 10 pulses	± 30	kV		
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C	
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT24				
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	I <sub>PPM</sub>	5	А
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	P <sub>PP</sub>	235	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	± 30	kV
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C

### Vishay Semiconductors

## Single-Line ESD-Protection in SOT-23



ABSOLUTE MAXIMUM RATINGS GSOT36					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$ ; single shot	I <sub>PPM</sub>	3.5	Α	
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t <sub>p</sub> = 8/20 μs; single shot	P <sub>PP</sub>	248	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	$V_{ESD}$	± 30	kV	
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	$T_J$	- 40 to + 125	°C	
Storage temperature		T <sub>STG</sub>	- 55 to + 150	°C	

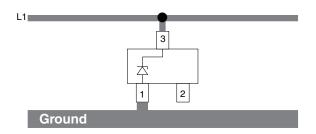
#### **BIAs-MODE** (1-line bidirectional asymmetrical protection mode)

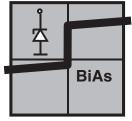
With the GSOTxx one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 3 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified maximum reverse working voltage (V<sub>RWM</sub>) the protection diode between pin 1 and pin 3 offer a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the break through voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The clamping voltage  $(V_C)$  is defined by the breakthrough voltage  $(V_{BR})$  level plus the voltage drop at the series impedance (resistance and inductance) of the protection device.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction of the protection diode. The low forward voltage  $(V_F)$  clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxx clamping behaviour is bidirectional and asymmetrical (BiAs).





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ELECTRICAL CHARACTERISTICS GSOT03						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	=.	-	1	lines
Reverse working voltage	at I <sub>R</sub> = 100 μA	$V_{RWM}$	3.3	-	-	V
Reverse current	at V <sub>R</sub> = 3.3 V	I <sub>R</sub>	-	-	100	μΑ
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	4	4.6	-	V
Payaraa alamaina valtaga	at I <sub>PP</sub> = 1 A	W	-	5.7	7.5	V
Reverse clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V <sub>C</sub>	-	1 3.3 100 4 4.6 5.7 7.5 - 10 12.3 - 1 1.2 - 4.5 420 600	V	
Compand alamanian valtage	at I <sub>PP</sub> = 1 A	V	-	1	1.2	V
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	V <sub>F</sub>	-	4.5	-	V
Canacitanas	at V <sub>R</sub> = 0 V; f = 1 MHz	0	-	420	600	pF
Capacitance	at V <sub>R</sub> = 1.6 V; f = 1 MHz	C <sub>D</sub>	_	260	-	pF

#### Note

• BiAs mode (between pin 3 and pin 1)



## Single-Line ESD-Protection in SOT-23

## Vishay Semiconductors

ELECTRICAL CHARACTERISTICS GSOT04						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines
Reverse working voltage	at I <sub>R</sub> = 20 μA	$V_{RWM}$	4	-	-	V
Reverse current	at V <sub>R</sub> = 4 V	I <sub>R</sub>	=	-	20	μΑ
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	5	6.1	-	V
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V	=	7.5	9	V
neverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	V <sub>C</sub>	=	11.2	14.3	V
Forward clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>F</sub>	=	6.1 7.5 11.2 1 1 4.5	1.2	V
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A	VF	=	4.5	-	V
Canacitanas	at V <sub>R</sub> = 0 V; f = 1 MHz		-	310	450	pF
Capacitance	at V <sub>R</sub> = 2 V; f = 1 MHz	C <sub>D</sub>	-	200	-	pF

#### Note

• BiAs mode (between pin 3 and pin 1)

ELECTRICAL CHARACTERISTICS GSOT05							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	=	-	1	lines	
Reverse working voltage	at I <sub>R</sub> = 10 μA	$V_{RWM}$	5	-	-	V	
Reverse current	at V <sub>R</sub> = 5 V	I <sub>R</sub>	=	-	10	μΑ	
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	6	6.8	-	V	
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	- V <sub>C</sub>	=	7	8.7	V	
	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A		=	12	16	V	
Forward clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>F</sub>	=	1	1.2	V	
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 30 A		=	4.5	-	V	
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	-	=	260	350	pF	
	at V <sub>R</sub> = 2.5 V; f = 1 MHz	C <sub>D</sub>	=	150		pF	

#### Note

• BiAs mode (between pin 3 and pin 1)

ELECTRICAL CHARACTERISTICS GSOT08							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines	
Reverse working voltage	at I <sub>R</sub> = 5 μA	$V_{RWM}$	8	-	-	V	
Reverse current	at V <sub>R</sub> = 8 V	I <sub>R</sub>	-	-	5	μΑ	
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	9	10	-	V	
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>C</sub>	-	10.7	13	V	
	at I <sub>PP</sub> = I <sub>PPM</sub> = 18 A		-	15.2	19.2	V	
Famuurd alamaning valtage	at I <sub>PP</sub> = 1 A	,,	-	1	1.2	V	
Forward clamping voltage	mping voltage at I <sub>PP</sub> = I <sub>PPM</sub> = 18 A	-	3	-	V		
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	160	250	pF	
	at V <sub>R</sub> = 4 V; f = 1 MHz		-	80	-	pF	

#### Note

• BiAs mode (between pin 3 and pin 1)

### **GSOT03 to GSOT36**

## Vishay Semiconductors

## Single-Line ESD-Protection in SOT-23



ELECTRICAL CHARAC	FERISTICS GSOT12					
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	ı	-	1	lines
Reverse working voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	12	-	-	V
Reverse current	at V <sub>R</sub> = 12 V	I <sub>R</sub>	1	-	1	μΑ
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	13.5	15	-	V
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	- V <sub>C</sub>	-	15.4	18.7	V
heverse clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 12 A		-	21.2	26	V
Forward elemping voltage	at I <sub>PP</sub> = 1 A	V <sub>F</sub>	=	1	1.2	V
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 12 A		-	2.2	-	V
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	0	=	115	150	pF
	at V <sub>R</sub> = 6 V; f = 1 MHz	- C <sub>D</sub>	ı	50	-	pF

#### Note

• BiAs mode (between pin 3 and pin 1)

ELECTRICAL CHARACTERISTICS GSOT15							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines	
Reverse working voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	15	-	-	V	
Reverse current	at V <sub>R</sub> = 15 V	I <sub>R</sub>	-	-	1	μΑ	
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	16.5	18	-	V	
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>C</sub>	-	19.4	23.5	V	
	at I <sub>PP</sub> = I <sub>PPM</sub> = 8 A		-	24.8	28.8	V	
Forward elemping voltage	at I <sub>PP</sub> = 1 A	V <sub>F</sub>	-	1	1.2	V	
Forward clamping voltage	at I <sub>PP</sub> = I <sub>PPM</sub> = 8 A		-	1.8	-	V	
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	0	-	90	120	pF	
	at V <sub>R</sub> = 7.5 V; f = 1 MHz	C <sub>D</sub>	-	35	-	pF	

#### Note

• BiAs mode (between pin 3 and pin 1)

ELECTRICAL CHARACTERISTICS GSOT24						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines
Reverse working voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	24	-	-	V
Reverse current	at V <sub>R</sub> = 24 V	I <sub>R</sub>	-	-	1	μΑ
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	27	30	-	V
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>C</sub>	-	34	41	V
	at I <sub>PP</sub> = I <sub>PPM</sub> = 5 A		-	41	47	V
Forward clamping voltage	at I <sub>PP</sub> = 1 A	V <sub>F</sub>	-	1	1.2	V
Forward clamping voltage	at $I_{PP} = I_{PPM} = 5 A$		-	1.4	-	V
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	- C <sub>D</sub>	-	65	80	pF
	at V <sub>B</sub> = 12 V; f = 1 MHz		-	20	-	рF

#### Note

• BiAs mode (between pin 3 and pin 1)



## Single-Line ESD-Protection in SOT-23

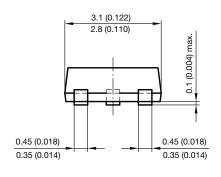
### Vishay Semiconductors

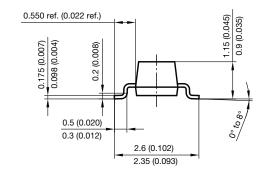
ELECTRICAL CHARACTERISTICS GSOT36							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines	
Reverse working voltage	at I <sub>R</sub> = 1 μA	$V_{RWM}$	36	-	-	V	
Reverse current	at V <sub>R</sub> = 36 V	I <sub>R</sub>	-	-	1	μΑ	
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	$V_{BR}$	39	43	-	V	
Reverse clamping voltage	at I <sub>PP</sub> = 1 A	- V <sub>C</sub>	-	49	60	V	
	at I <sub>PP</sub> = I <sub>PPM</sub> = 3.5 A		-	59	71	V	
Converd elemening voltage	at I <sub>PP</sub> = 1 A	.,	-	1	1.2	V	
Forward clamping voltage	ing voltage $at I_{PP} = I_{PPM} = 3.5 A$	VF	-	1.3	-	V	
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	-	-	52	65	pF	
	at V <sub>R</sub> = 18 V; f = 1 MHz	- C <sub>D</sub>	-	12	-	pF	

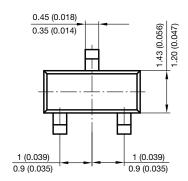
#### Note

• BiAs mode (between pin 3 and pin 1)

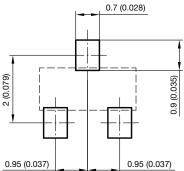
#### **PACKAGE DIMENSIONS** in millimeters (inches): **SOT-23**











Document no.: 6.541-5014.01-4 Rev. 8 - Date: 23.Sept.2009

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